

General Description

The AON7428 uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is ideal for load switch and battery protection applications.

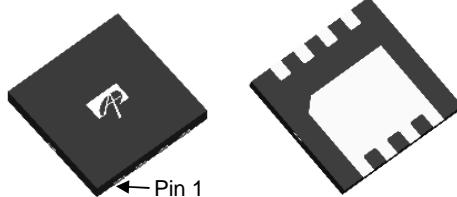
Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	50A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 2.8mΩ
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 3.6mΩ

100% UIS Tested
100% R_g Tested

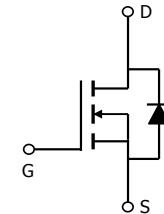


Top View



Bottom

Top View



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	50	A
$T_C=100^\circ C$		39	
Pulsed Drain Current ^C	I_{DM}	250	
Continuous Drain Current	I_{DSM}	34	A
$T_A=70^\circ C$		27	
Avalanche Current ^C	I_{AR}, I_{AS}	50	A
Repetitive avalanche energy $L=0.1mH$ ^C	E_{AR}, E_{AS}	125	mJ
Power Dissipation ^B	P_D	83	W
$T_C=100^\circ C$		33	
Power Dissipation ^A	P_{DSM}	6.2	W
$T_A=70^\circ C$		4	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	16	20	°C/W
Maximum Junction-to-Ambient ^{A,D}		45	55	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1.1	1.5	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	30	36		V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			100	nA
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.1	1.7	2.3	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	250			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$ $T_J=125^\circ\text{C}$		2.3 3.8	2.8 4.6	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=20\text{A}$		2.9	3.6	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=20\text{A}$		100		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.7	1	V
I_S	Maximum Body-Diode Continuous Current ^G				50	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$	2080	2600	3120	pF
C_{oss}	Output Capacitance		300	430	560	pF
C_{rss}	Reverse Transfer Capacitance		170	280	390	pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	1.7	3.5	5	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, I_D=20\text{A}$	40	49	60	nC
$Q_g(4.5\text{V})$	Total Gate Charge		20	24	30	nC
Q_{gs}	Gate Source Charge		8	10	12	nC
Q_{gd}	Gate Drain Charge		5	8	11	nC
$t_{\text{D(on)}}$	Turn-On DelayTime	$V_{GS}=10\text{V}, V_{DS}=15\text{V}, R_L=0.75\Omega, R_{\text{GEN}}=3\Omega$		7		ns
t_r	Turn-On Rise Time			10		ns
$t_{\text{D(off)}}$	Turn-Off DelayTime			58		ns
t_f	Turn-Off Fall Time			20		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}, dI/dt=500\text{A}/\mu\text{s}$	14	18	22	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}, dI/dt=500\text{A}/\mu\text{s}$	30	37	45	nC

A. The value of R_{0JA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on R_{0JA} $t \leq 10\text{s}$ value and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.

D. The R_{0JA} is the sum of the thermal impedance from junction to case R_{0JC} and case to ambient.

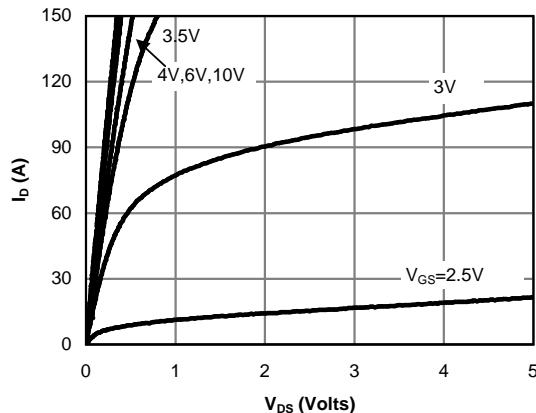
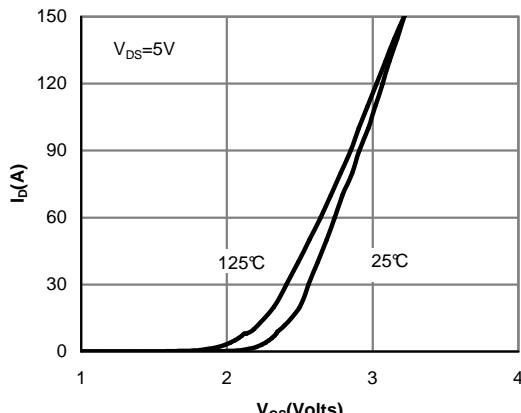
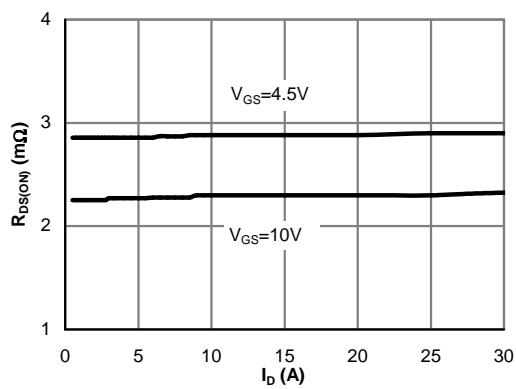
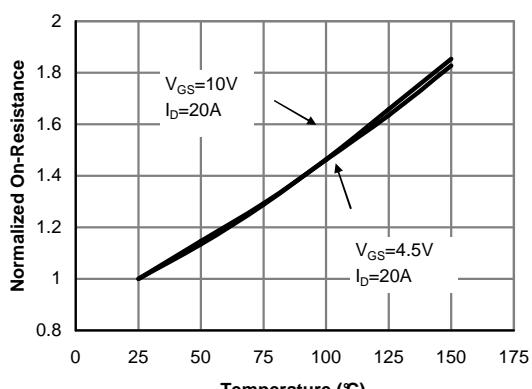
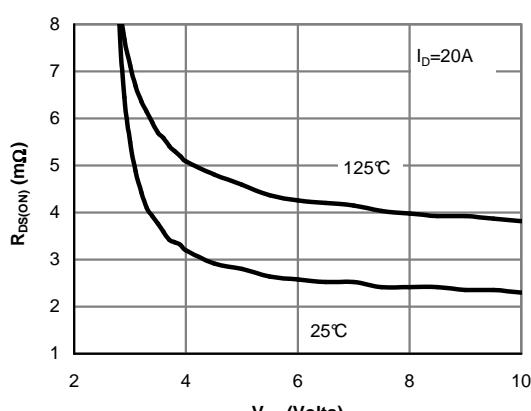
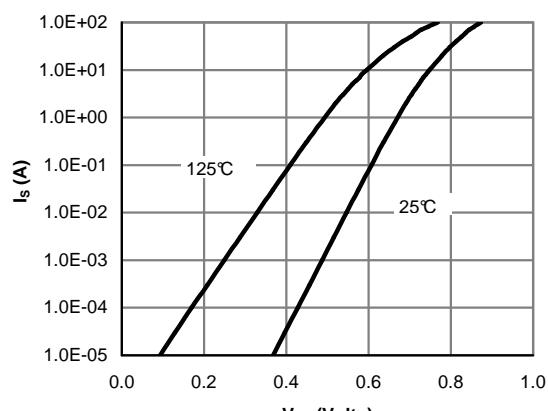
E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

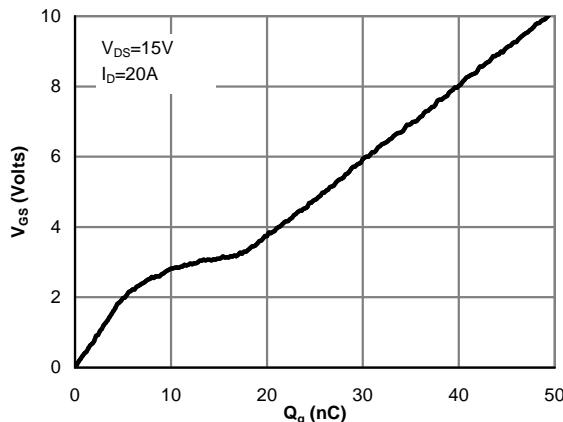
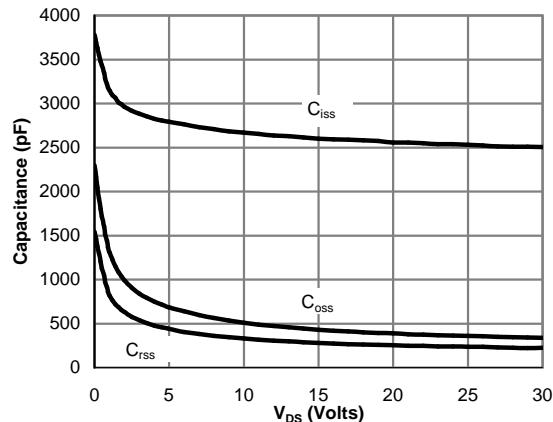
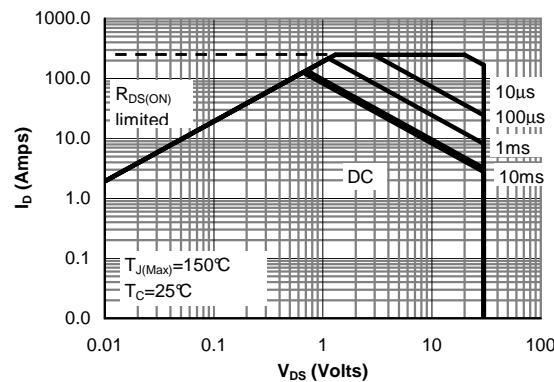
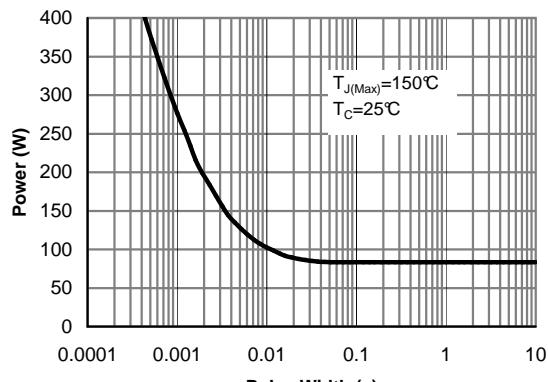
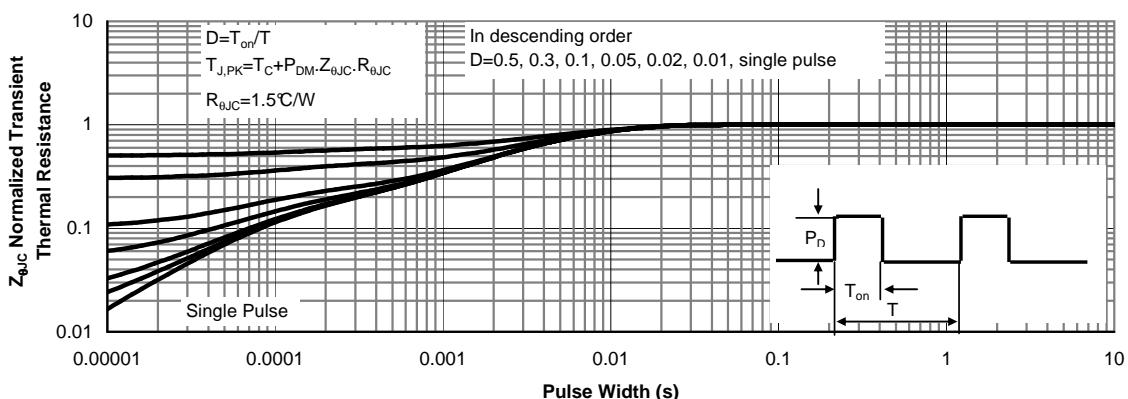
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(\text{MAX})}=150^\circ\text{C}$. The SOA curve provides a single pulse rating.

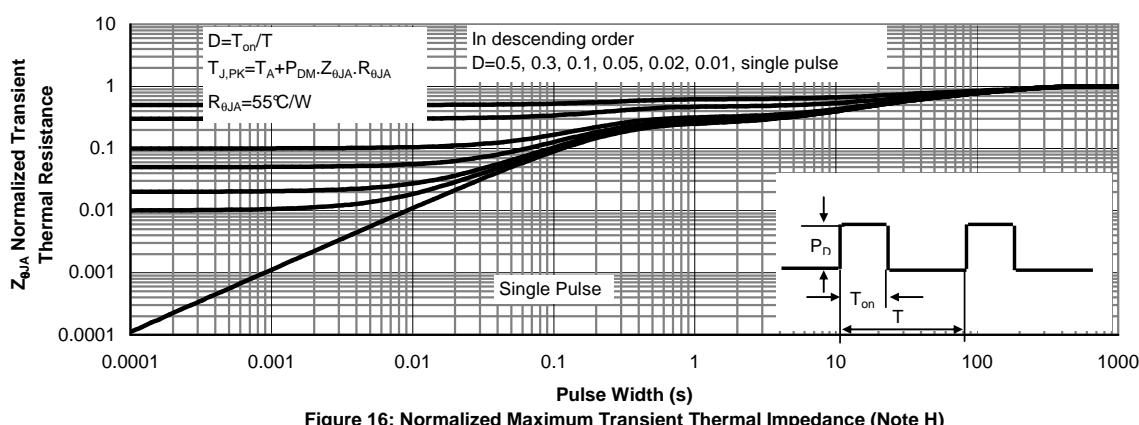
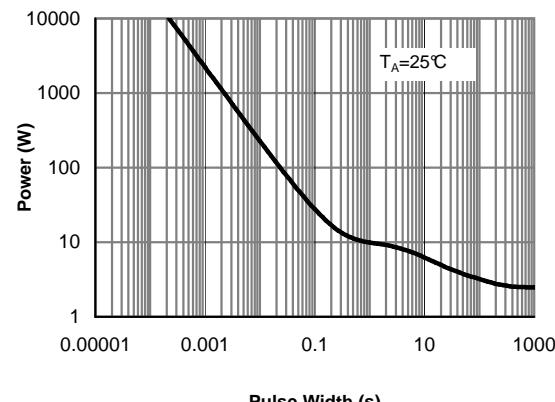
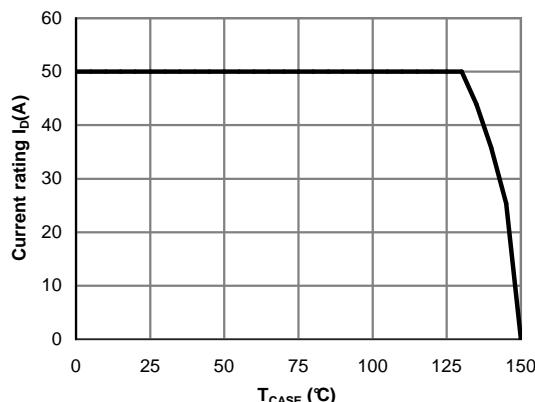
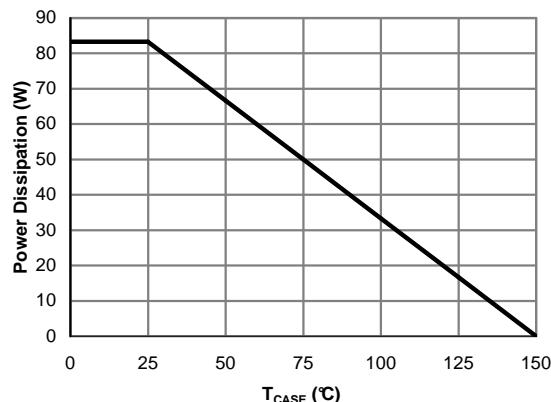
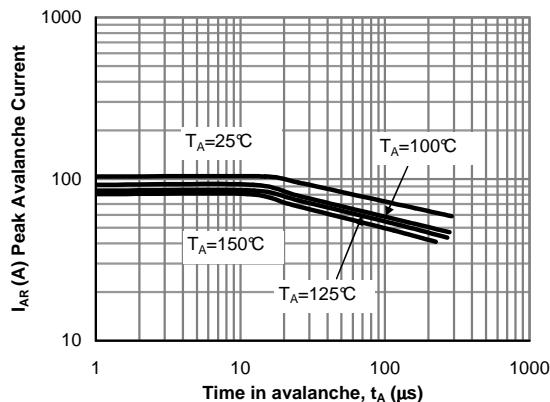
G. The maximum current rating is limited by package.

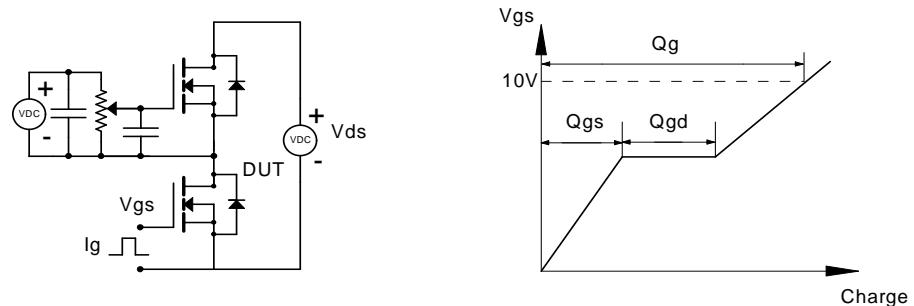
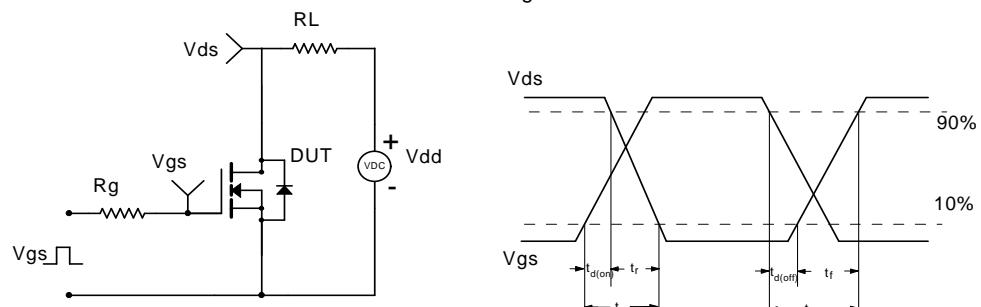
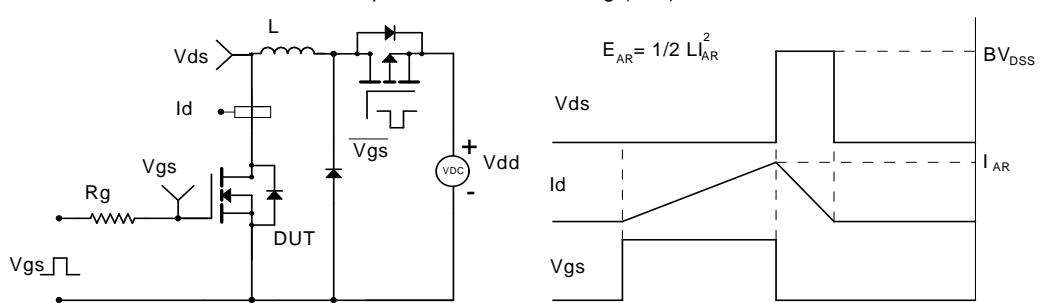
H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Fig 1: On-Region Characteristics (Note E)

Figure 2: Transfer Characteristics (Note E)

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

Figure 4: On-Resistance vs. Junction Temperature (Note E)

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

Diode Recovery Test Circuit & Waveforms
